PROCESS CPZ18

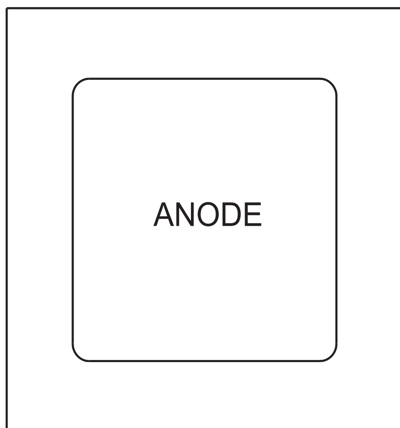
Zener Diode

0.5 Watt Zener Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	13.8 x 13.8 MILS
Die Thickness	7.5 MILS
Anode Bonding Pad Area	7.5 x 7.5 MILS
Top Side Metalization	Al - 13,000Å
Back Side Metalization	Au - 14,000Å

GEOMETRY



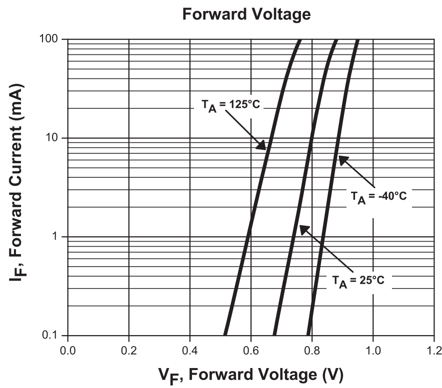
BACKSIDE CATHODE R0

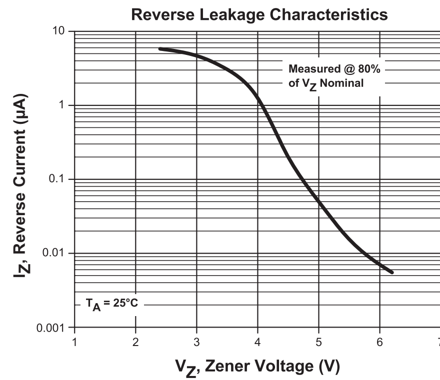
GROSS DIE PER 4 INCH WAFER
61,141

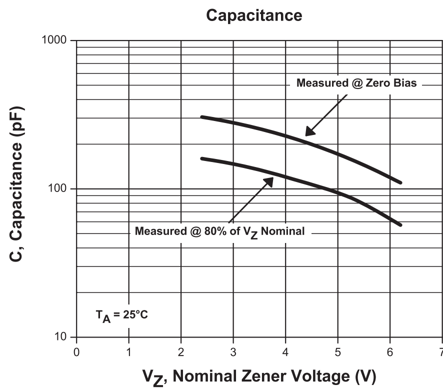
PRINCIPAL DEVICE TYPES
CMPZ5221B
THRU
CMPZ5234B

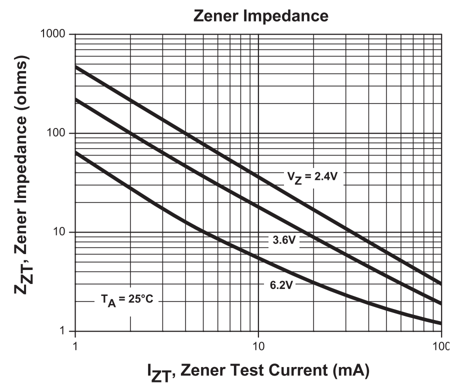
PROCESS CPZ18

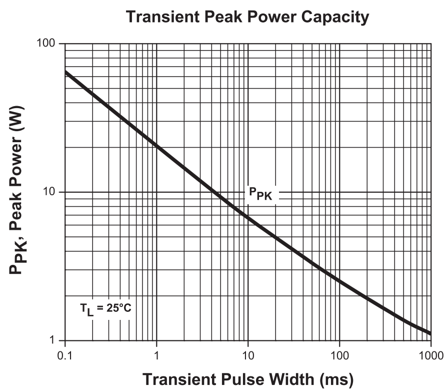
Typical Electrical Characteristics

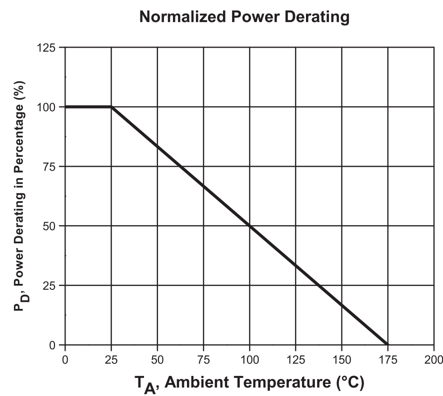












R6 (22-March 2010)